

Properties of carbon-infused silicon LGAD devices after non-uniform irradiation with 24 GeV/c protons

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Abstract

Forward proton spectrometers at high-energy proton colliders rely on precision timing to discriminate signal from background. Silicon low gain avalanche diodes (LGADs) are a candidate for future timing detectors in these systems. A major challenge for the use of LGADs is that these detectors must be placed within a few mm of the beams, resulting in a very large and highly non-uniform radiation environment. We present a first measurement of the current and capacitance vs. voltage behavior of LGAD sensors, after a highly non-uniform irradiation with beams of 24 GeV/c protons at fluences up to $1 \times 10^{16} p/cm^2$.

Keywords: Low Gain Avalanche Diode, LGAD, Non-Uniform Irradiation

1. Introduction

At the CERN Large Hadron Collider (LHC), forward proton detectors rely on precision timing measurements to distinguish signal events from "pileup" (multiple collisions in the same bunch crossing) backgrounds. The CMS-TOTEM PPS and ATLAS-AFP projects pioneered precision proton timing in Run 2 of the LHC, using synthetic single-crystal diamond [1, 2, 3, 4, 5, 6, 7] and quartz Cherenkov [8, 9] technologies, respectively. Initial

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studies were also performed with silicon low gain avalanche diode (LGAD) detectors [10] in 2017.

Since the early LGAD studies, the technology has matured, and is now the choice for the endcap timing layer upgrades of the CMS and ATLAS experiments [11, 12, 13]. This also makes them an attractive candidate for use in forward proton detectors at the High-Luminosity LHC (HL-LHC) [14]. A major challenge for using LGADs in forward proton detectors is the radiation environment, which is both large and highly non-uniform, due to the proximity to the beam. While many previous studies have investigated the behavior of LGADs after irradiation with reactor neutrons or proton beams [15, 16, 17, 18, 19, 20, 21], these have focused on the case of uniform irradiation, with a single device irradiated to a fixed amount. In this paper we aim to evaluate the behavior after highly non-uniform irradiation with high-energy protons, to understand whether a single device can be operated after very different internal radiation doses.

2. Radiation environment

Forward proton detectors at the LHC are placed extremely close to the beam, at distances of a few mm. The sensor planes are oriented perpendicular to the beam, with one edge near the beam and the other edge farther away. This results in a highly non-uniform irradiation environment [22, 14], with more than an order of magnitude variation over distances of a few cm. At the High-Luminosity LHC, the sensors will be exposed to peak radiation doses of order $1 \times 10^{16} p/cm^2$ in the region closest to the beam.

3. LGAD sensors

The LGAD sensors used for this study were produced by Fondazione Bruno Kessler (FBK), as part of the UFSD4 production. They have pixels of area $1.3 \times 1.3 mm^2$, with a total area defined by an array of 5x5 pixels. An example of a 5x5 LGAD used for this study is shown in Fig. 1.

All of the sensors used in this study originate from wafer 18 of the FBK UFSD4 production, which was observed to be the most radiation hard of this production in uniform irradiation tests. These sensors are designed with a deep gain layer, enriched with carbon to help mitigate the acceptor removal effect produced by radiation [16]. The properties of UFSD4 and wafer 18 are discussed in more detail in Ref. [12].

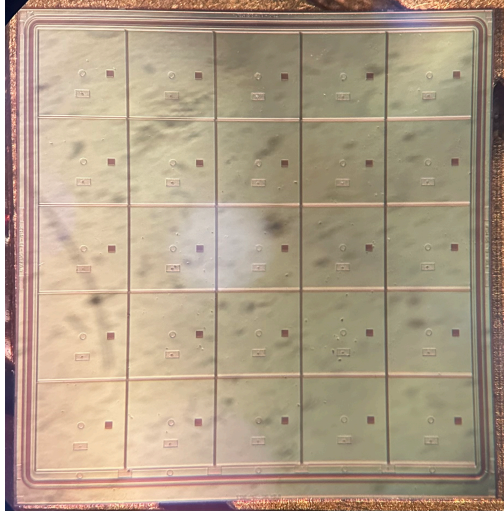


Figure 1: One 5x5 LGAD used for this study, photographed under a microscope. The 5x5 square array of pixels is visible, inside the guard ring. The rectangular areas are the IV probe contact points for the pixels and the guard rings.

In these sensors, a single bias voltage is provided to all pixels, as is typical of LGADs planned for the LHC experiments. This design imposes significant constraints on the HV operating point. The HV must be large enough that the most irradiated regions of the detector still perform well, but small enough that the least irradiated regions do not go into breakdown.

4. Irradiation conditions

The irradiation was performed at the IRRAD facility [24, 25] at the CERN Proton Synchrotron (PS). This provides high-intensity proton beams with an energy of 24 GeV/c. In order to produce a non-uniform gradient, the sensors were offset from the beam center in both the horizontal and vertical directions (Fig. 2), creating a large variation in the dose along the diagonal going from the lower left to upper right of the sensor.

A total of five sensors were tested. Two of the sensors were irradiated to reach a peak dose at the center of the beam corresponding to approximately 1×10^{16} p/cm². Two other sensors were removed at the halfway point of the irradiation, resulting in a peak dose of approximately 5×10^{15} p/cm². The final sensor was not irradiated, and served as a control sample. The actual

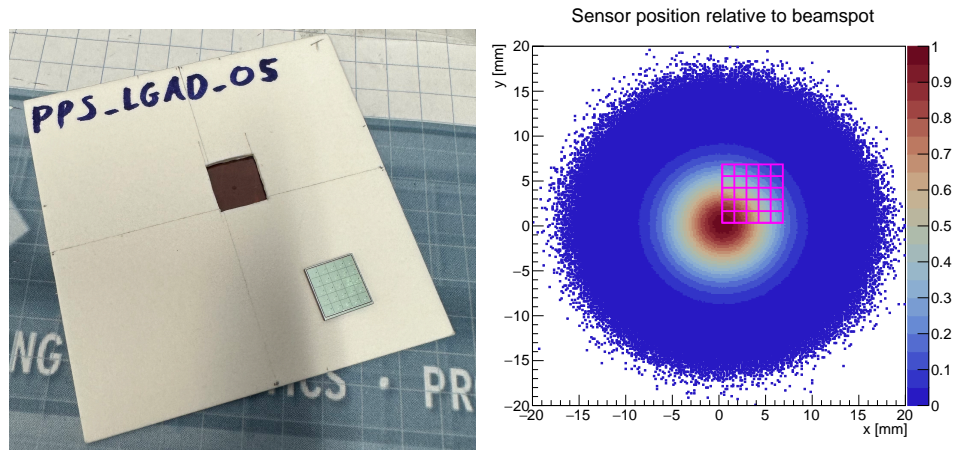


Figure 2: Left: 5x5 LGAD sensor (seen before mounting at lower right) and frame used to mount the sensor for irradiation. The beam is centered at the center of the white square frame, with the sensor placed in the hole covered by kapton film. Right: Approximate positioning of sensors in the IRRAD beam. The squares indicate the positioning of the 5x5 LGAD device. The histogram indicates the beamspot shape during the period of irradiation, estimated from beam position monitoring data, with the colors indicating the relative intensity.

dose was cross-checked using measurements of activated foils placed in the beamline. The dose measured at the center of the beam was found to be 3 – 11% higher than the nominal target, with an uncertainty of 7%.

The irradiation gradient was estimated from beam position monitoring (BPM) measurements at the IRRAD facility. These measurements were used to generate a two-dimensional representation of the beamspot, and the corresponding radiation profile within the sensors under test. As shown in Fig. 3, there is approximately a factor of 2 in dose between the most irradiated pixel and the pixel at the center of the sensor, and a factor of 10 in dose between the most irradiated pixel and the least irradiated pixel.

5. Measurement conditions

The IV and CV measurements were conducted with a probe station at the CERN Solid State Detectors lab. A single probe was kept in contact with the guard ring and connected to ground, while a second probe was used to measure the pixel of interest. The bias voltage was applied from the back side of the LGAD device, through the chuck.

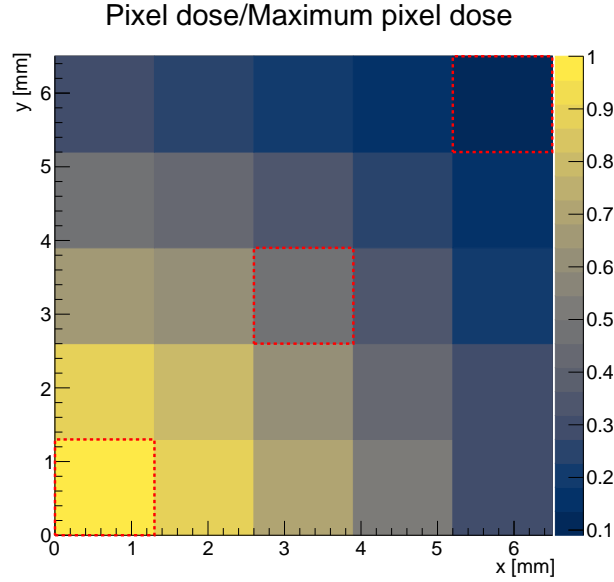


Figure 3: Relative dose integrated in each pixel of the LGADs, compared to the most irradiated pixel. Each box in the plot represents a single $1.3 \times 1.3\text{mm}^2$ pixel. The pixels for which IV curves are measured are shown by the dashed boxes at lower left, center, and upper right. The dimensions of the LGAD are approximate, and do not show the size of the guard ring or interpad spacing.

Prior to irradiation, the measurements were done both at room temperature, and at -20°C , consistent with the expected operating temperature of the LGADs. After irradiation, the measurements were performed only at -20°C , and the samples were also stored at -20°C to limit annealing effects. In the following we focus only on the measurements performed at -20°C , in order to compare the results before and after irradiation in the same conditions.

The measurements were done by increasing the voltage from zero to the maximum, and then decreasing from the maximum to zero to check for hysteresis effects. The maximum voltage was chosen to be in a safe range such that the sensors did not approach breakdown. This maximum was between 200V and 400V, depending on the sensor and radiation dose.

6. Results

The LGAD IV curves were measured before and after irradiation. The focus was on pixels positioned on the diagonal of the LGAD sensor, which followed the direction of the irradiation gradient. Specifically pixels [0,0], [2,2], and [4,4] were measured, where [0,0] is located at the bottom left and [4,4] at the upper right of the sensor shown in Figure 3. In this way the most-irradiated and least-irradiated pixels were tested, as well as a pixel with an intermediate radiation dose.

6.1. IV measurements before and after irradiation

Fig. 4 shows the current as a function of voltage for the sensor that was not irradiated. Figures 5 and 6 show the IV curves for three pixels on each of the four devices under test, before and after irradiation. All of the plotted measurements were performed with the sensors cooled to -20°C .

Prior to irradiation, all pixels measured show generally similar behavior. A steep increase is observed, reaching a sharp "knee" around 50 V, as the sensor reaches full depletion voltage. This is followed by a plateau-like behavior with a slow increase of currents up to around 0.1 nA. At higher voltages, at approximately 200 V, the current shows a runaway increase as it approaches the breakdown voltage.

After irradiation, the effect of the non-uniformity is clear, as the least irradiated pixel maintains the sharpest turn-on. The more irradiated pixels display a shallower turn-on, and operating voltages with currents of order $1\ \mu\text{A}$. The most irradiated pixels also do not show any sign of a rapid increase toward breakdown, up to the highest values measured (350 V). In all cases the currents at the operating voltages after irradiation are 3-4 orders of magnitude larger than pre-irradiation.

6.2. Operating voltage ranges

Operating the sensors with a single high voltage setting under non-uniform irradiation requires a working point where the most irradiated areas of the sensor are above the full depletion voltage, while the least irradiated areas of the sensor are safely below breakdown.

In order to quantify the operating voltage range, we analyze the shape of the IV curves. A cubic spline interpolation is performed between consecutive voltage points, using 5 V steps to smooth fluctuations. The derivative dI/dV is then calculated based on the interpolation. The derivative has a

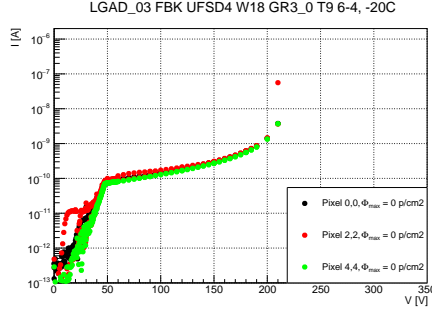


Figure 4: IV curves for the non-irradiated sensor, measured for three pixels along the diagonal. The black, red, and green points represent the pixels along the diagonal in positions $[0,0]$, $[2,2]$, and $[4,4]$, respectively.

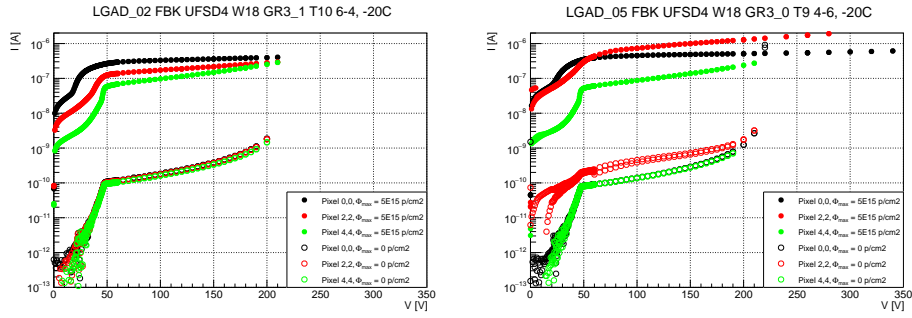


Figure 5: IV curves before and after irradiation, measured for three pixels along the direction of the irradiation gradient, for two devices irradiated to a maximum of $5 \times 10^{15} p/cm^2$. The open markers represent the measurement before irradiation, the closed markers the measurement after irradiation. The black, green, and red points represent the most irradiated, least irradiated, and an intermediate pixel, respectively.

sharp peak corresponding to the sharp rise of current as the bulk becomes activated, followed by a plateau-like behavior above the knee. For the less irradiated pixels, the derivative begins increasing again at higher voltages as the sensor approaches the breakdown region. For the most irradiated pixels, the derivative remains roughly constant up to the highest voltages tested. We consider the range between the initial peak in the derivative and the second increase at larger voltages as the operating range for each pixel. The procedure is illustrated in Figures 7 and 8 for two pixels of one LGAD device, before and after irradiation.

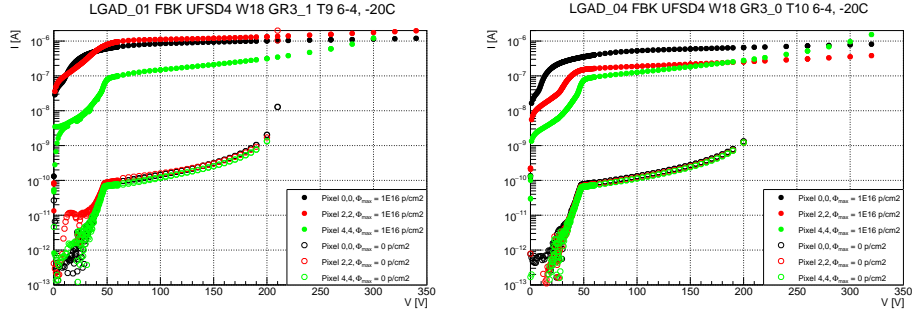


Figure 6: IV curves before and after irradiation, measured for three pixels along the direction of the irradiation gradient, for two devices irradiated to a maximum of $1 \times 10^{16} p/cm^2$. The open markers represent the measurement before irradiation, the closed markers the measurement after irradiation. The black, green, and red points represent the most irradiated, least irradiated, and an intermediate pixel, respectively.

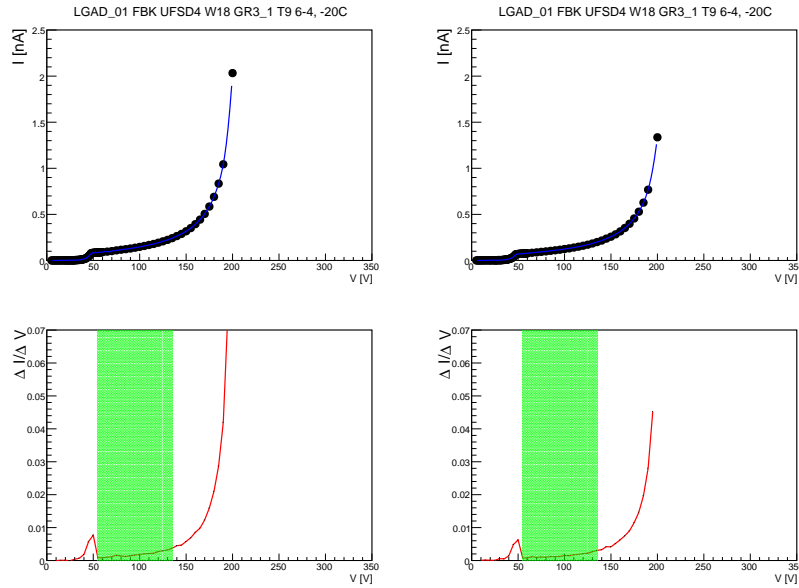


Figure 7: IV curves for pixels 0,0 (left) and 4,4 (right) of device 1, before irradiation. The measured points and spline interpolation are shown above, and the derivative of the interpolation is shown below. The shaded region in the lower plots indicates the operational voltage range.

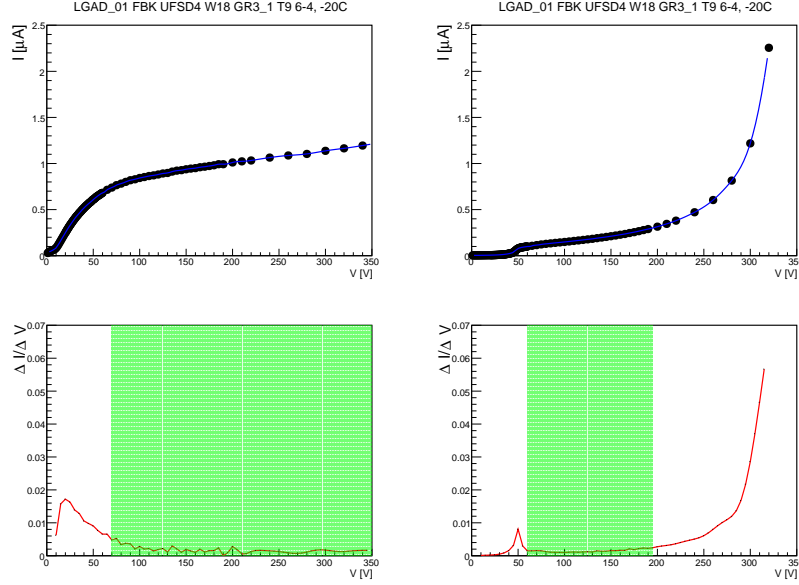


Figure 8: IV curves for pixels 0,0 (left) and 4,4 (right) of device 1, after irradiation with a maximum dose of $1 \times 10^{16} p/cm^2$. Pixel 0,0 is near the beam center and receives the maximum dose, while Pixel 4,4 is farthest from the beam center. The measured points and spline interpolation are shown above, and the derivative of the interpolation is shown below. The shaded region in the lower plots indicates the operational voltage range.

In Table 1, the upper and lower operating voltages obtained are listed for each pixel under test, before and after irradiation. In cases where no increase of the derivative corresponding to breakdown is observed, the maximum voltage tested is shown as a lower limit.

Prior to irradiation, this procedure finds a minimum operating voltage for almost all pixels close to 55 V. The maximum, determined by the point where the slope of the IV curve starts rapidly increasing, is in most cases between 135 V and 145 V. After irradiation, the minimum voltages range from 50 V to 85 V, depending on the sensor and radiation dose received. For the least irradiated pixels, the maximum voltages are between 180 V and 200 V, while for the most irradiated pixels no maximum is found up to the largest voltages measured (between 200 V and 400 V, depending on the device).

For all devices tested, the maximum V_{OP} of the least irradiated pixel is above the minimum V_{OP} of the most irradiated pixel, indicating that a com-

Device	Peak irradiation (p/cm ²)	Pixel	V_{OP} [V] pre-irradiation	V_{OP} [V] post-irradiation
1	1×10^{16}	0,0	55 - 135	70 - >400
		2,2	55 - 145	70 - >400
		4,4	55 - 135	60 - 195
2	5×10^{15}	0,0	55 - 145	50 - >200
		2,2	55 - 135	55 - >200
		4,4	55 - 140	55 - 185
3	0	0,0	55 - 135	N/A
		2,2	55 - 140	N/A
		4,4	55 - 135	N/A
4	1×10^{16}	0,0	55 - 135	65 - >320
		2,2	55 - 135	55 - >320
		4,4	55 - 140	55 - 195
5	5×10^{15}	0,0	55 - 135	60 - >400
		2,2	55 - 110	85 - 200
		4,4	55 - 135	55 - 180

Table 1: Operating voltage ranges of LGAD sensors before and after irradiation, based on IV curve shapes. For each sensor, the minimum and maximum voltages are shown for 3 pixels along the irradiation gradient, before and after irradiation. The ranges are determined by analyzing the derivative of the interpolation of the measured data points for each pixel.

mon operating voltage range is possible with an order of magnitude gradient in the radiation dose. The minimum V_{OP} of the most irradiated pixels is also below the maximum V_{OP} of the non-irradiated pixels.

6.3. Gain Layer Voltage and Acceptor Removal

The mechanism of radiation damage on LGADs is believed to be at least partly related to the removal of boron doping atoms, resulting in an effective degradation or removal of acceptors.

In order to study the acceptor removal from the IV curves, we use the k-factor method [26]. This is similar to the dI/dV derivative method used to define the operating voltage range, except the derivative is multiplied by the ratio of current to voltage to obtain the dimensionless quantity:

$$k = dI/dV * V/I$$

The first maximum of this function occurs at decreasing voltages, as the irradiation dose increases and a larger fraction of acceptors are removed. The maximum of the k-factor below breakdown is used to define the gain layer voltage, V_{GL} . The acceptor removal function is then defined by the ratio $V_{GL}(\Phi)/V_{GL}(0)$, where Φ represents the radiation dose, $V_{GL}(\Phi)$ is the gain layer voltage at a given radiation dose, and $V_{GL}(0)$ is the gain layer voltage prior to irradiation.

Figure 9 shows the calculated acceptor removal fraction, as a function of the approximate radiation dose accumulated on each pixel. The approximate dose on each pixel, plotted on the x axis, is estimated from the beamspot profiles (Fig. 3). The measured pixels reveal a consistent acceptor removal fraction as a function of the irradiated dose, despite belonging to different sensors.

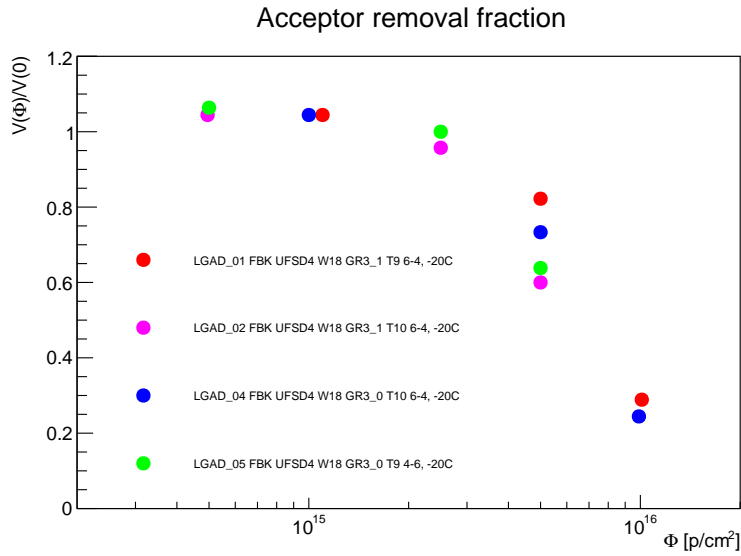


Figure 9: Acceptor removal determined from IV curves, for pixels exposed to different radiation levels. The two sensors exposed to a maximum of 1×10^{16} p/cm² are shown by the red and blue points. The two sensors exposed to a maximum of 5×10^{15} p/cm² are represented by the purple and green points.

6.4. CV measurements before and after irradiation

For one of the sensors irradiated to the maximum peak dose of 1×10^{16} p/cm², capacitance versus voltage measurements were made before and after irradiation.

ation, at -20°C . The capacitance was measured up to voltages of 65 V, again with both increasing and decreasing voltages to check for hysteresis effects. The same measurements were also performed for the non-irradiated sensor.

The results are shown in Fig. 10, plotted as $1/C^2$ vs. voltage. For the non-irradiated sensor, all pixels show a similar behavior, with a nearly flat curve as the gain layer is activated, followed by a sharp turn-on around 45 V as the bulk becomes depleted, followed by a plateau around 50 V after the sensor reaches full depletion. This value is compatible with the minimum operating voltages obtained from the analysis of the IV curves before irradiation. The other sensor that was irradiated to the maximum fluence shows very similar behavior prior to irradiation.

After irradiation, the voltage at which the gain layer is depleted is observed to decrease for the more irradiated pixels, while the slope during the depletion of the bulk becomes shallower. The capacitance at the lowest voltages is observed to decrease for all pixels after irradiation, consistent with a decreasing depth of the gain layer. This behavior within a single device is qualitatively similar to Refs. [20, 16], where different devices were tested with different uniform radiation doses. For the most irradiated pixel, the capacitance does not reach a clear plateau up to the maximum voltage of 65 V. For the less irradiated pixels, receiving doses of $\sim 5 \times 10^{15} \text{p/cm}^2$ and $\sim 1 \times 10^{15} \text{p/cm}^2$, the minimum capacitance is reached by 65 V, slightly higher than the value seen before irradiation.

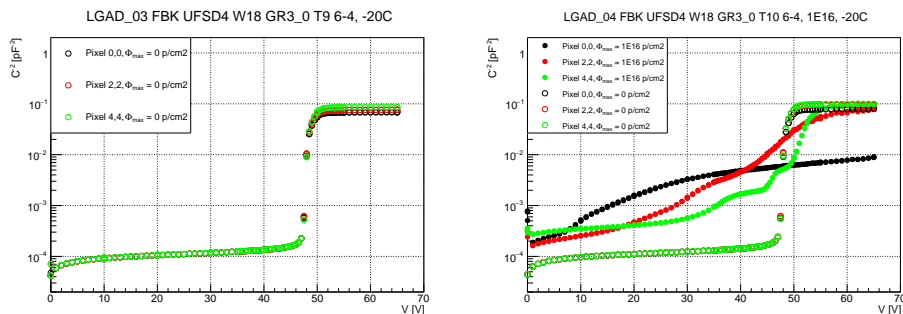


Figure 10: CV curves measured for two sensors at -20°C . Left: curves for the non-irradiated sensor, measured for three pixels along the diagonal. Right: curves before and after irradiation, measured for three pixels along the direction of the irradiation gradient, for one device irradiated to a maximum of $1 \times 10^{16} \text{p/cm}^2$. The open markers represent the measurement before irradiation, the closed markers the measurement after irradiation.

7. Conclusions

The use of silicon LGAD timing detectors for forward protons at the HL-LHC requires operation in a new radiation environment. Both the peak irradiation and the size of the non-uniform irradiation gradient are larger than expected for other applications, even at the HL-LHC.

A first measurement of carbon-infused LGAD current and capacitance vs. voltage properties was performed before and after non-uniform irradiation with 24 GeV/c proton beams at the CERN PS, with a peak dose of up to $1 \times 10^{16} \text{p/cm}^2$. A gradient of a factor ~ 10 , realistic for forward proton detectors, was achieved by offsetting the sensors from the beam center in the vertical and horizontal directions. After irradiation, all pixels were found to reach an operational voltage at or below 90 V, with currents of order $\sim 1 \mu\text{A}$ at a temperature of -20°C . The less irradiated pixels were observed to approach breakdown above 200 V. This indicates that a common high voltage working point may be found for all pixels in a sensor, in spite of the large differences in radiation dose.

Measurements of the CV curves for one sensor show that pixels irradiated up to approximately $5 \times 10^{15} \text{p/cm}^2$ reach a similar capacitance as non-irradiated pixels, at voltages about 5-10 V higher. For pixels irradiated up to $1 \times 10^{16} \text{p/cm}^2$, the capacitance remains larger after irradiation, up to the highest voltages measured. Future measurements will study the performance of sensors optimized for the forward proton timing application, and evaluate the efficiency and time resolution of sensors before and after irradiation.

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